

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (canceled).
2. (canceled).
3. (canceled).
4. (currently amended): A method for producing the an electrode as claimed in claim 1 adapted for use with a silicon carbide semiconductor, which electrode serves as an ohmic electrode and comprises a p-type silicon layer formed on the surface of a semiconductor formed from p-type silicon carbide, and a metal silicide layer formed on the p-type silicon layer, which method comprises forming the metal silicide layer by means of laser ablation.
5. (original): The method as claimed in claim 4, which further comprises subjecting the metal silicide layer to at least one of laser irradiation and heat treatment, subsequent to formation of the metal silicide layer by means of laser ablation.
6. (original): The method as claimed in claim 4, which further comprises subjecting the metal silicide layer to at least one of laser irradiation and heat treatment, subsequent to formation of the metal silicide layer by means of laser ablation; and then depositing a metal silicide on the surface of the laser-irradiated or heat-treated metal silicide layer by means of laser ablation.
7. (canceled).
8. (canceled).

9. (canceled).
10. (currently amended): A method for producing ~~the a~~ silicon carbide semiconductor element ~~as in claim 7 comprising: a semiconductor formed from p-type silicon carbide; and an electrode adapted for use with a silicon carbide semiconductor, the electrode comprising an ohmic electrode including p-type silicon layer formed on the surface of the p-type silicon carbide semiconductor, and a metal silicide layer formed on the p-type silicon layer,~~ which method comprises forming the metal silicide layer by means of laser ablation.
11. (original): The method as claimed in claim 10, which further comprises subjecting the metal silicide layer to at least one of laser irradiation and heat treatment, subsequent to formation of the metal silicide layer by means of laser ablation.
12. (original): The method as claimed in claim 10, which further comprises subjecting the metal silicide layer to at least one of laser irradiation and heat treatment, subsequent to formation of the metal silicide layer by means of laser ablation; and then depositing a metal silicide on the surface of the laser-irradiated or heat-treated metal silicide layer by means of laser ablation.